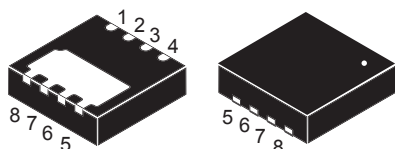
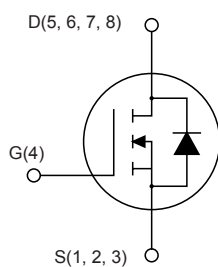


N-channel 600 V, 1.5 Ω typ., 2.2 A MDmesh II Power MOSFET in a PowerFLAT 3.3x3.3 HV package



PowerFLAT 3.3x3.3 HV



AM15810v1



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STL3NM60N	600 V	1.8 Ω	2.2 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Product status link

[STL3NM60N](#)

Product summary

Order code	STL3NM60N
Marking	3NM60
Package	PowerFLAT 3.3x3.3 HV
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	600	V
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	2.2	A
	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	1.7	
	Drain current (continuous) at $T_A = 25\text{ }^{\circ}\text{C}$	0.65	
	Drain current (continuous) at $T_A = 100\text{ }^{\circ}\text{C}$	0.5	
$I_{DM}^{(1)}$	Drain current pulsed	2.6	A
P_{TOT}	Total power dissipation at $T_A = 25\text{ }^{\circ}\text{C}$	2	W
	Total power dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	22	W
I_{AS}	Avalanche current, repetitive or non-repetitive (pulse width limited by T_J max)	1	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AS}$, $V_{DD} = 50\text{ V}$)	119	mJ
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
T_J	Operating junction temperature range	-55 to 150	$^{\circ}\text{C}$
T_{stg}	Storage temperature range		$^{\circ}\text{C}$

1. Pulse width is limited by safe operating area.

2. $I_{SD} \leq 2.2\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS}(\text{peak}) \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	5.6	$^{\circ}\text{C}/\text{W}$
$R_{thJA}^{(1)}$	Thermal resistance, junction-to-ambient	62.5	$^{\circ}\text{C}/\text{W}$

1. When mounted on an 1-inch² FR-4, 2 Oz copper board, $t < 10\text{ s}$.

2 Electrical characteristics

$T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 600\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 600\text{ V}$, $T_C = 125\text{ }^{\circ}\text{C}^{(1)}$			100	
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 1\text{ A}$		1.5	1.8	Ω

1. Defined by design, not subject to production test.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	188	-	pF
C_{oss}	Output capacitance		-	13	-	pF
C_{rss}	Reverse transfer capacitance		-	1.1	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent capacitance energy related	$V_{DS} = 0\text{ to }480\text{ V}$, $V_{GS} = 0\text{ V}$	-	100	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	6	-	Ω
Q_g	Total gate charge	$V_{DD} = 480\text{ V}$, $I_D = 2.2\text{ A}$	-	9.5	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 0\text{ to }10\text{ V}$	-	1.6	-	nC
Q_{gd}	Gate-drain charge	(see Figure 14. Test circuit for gate charge behavior)	-	5.3	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 1.1\text{ A}$,	-	8.6	-	ns
t_r	Rise time	$R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	6.2	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	20.8	-	ns
t_f	Fall time		-	20	-	ns

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		2.2	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		2.6	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2.2 \text{ A}$, $V_{GS} = 0 \text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 2.2 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 60 \text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	168		ns
Q_{rr}	Reverse recovery charge		-	672		nC
I_{RRM}	Reverse recovery current		-	8		A
t_{rr}	Reverse recovery time	$I_{SD} = 2.2 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 60 \text{ V}$, $T_J = 150 \text{ }^\circ\text{C}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	2.3		ns
Q_{rr}	Reverse recovery charge		-	913		nC
I_{RRM}	Reverse recovery current		-	9		A

1. Pulse width is limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

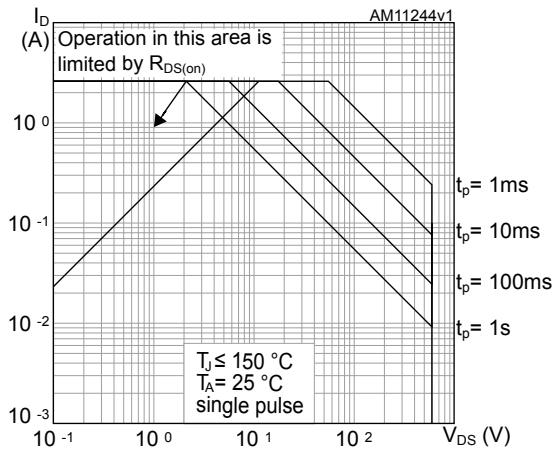


Figure 2. Normalized transient thermal impedance

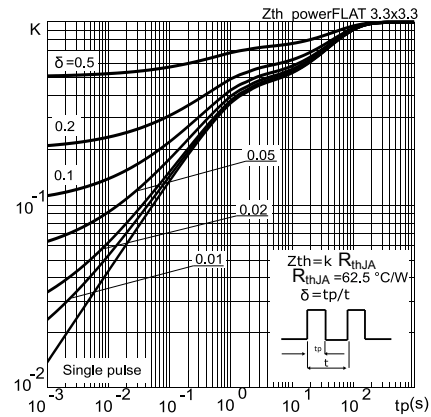


Figure 3. Typical output characteristics

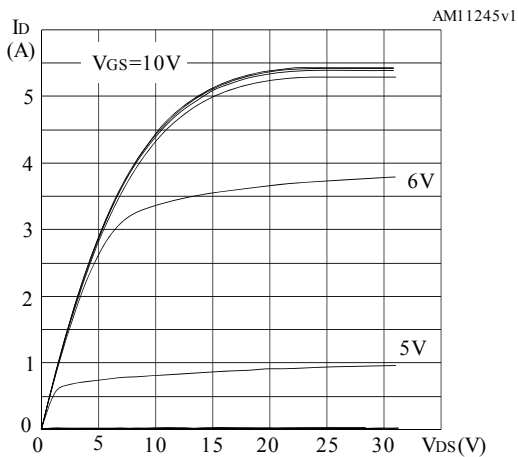


Figure 4. Typical transfer characteristics

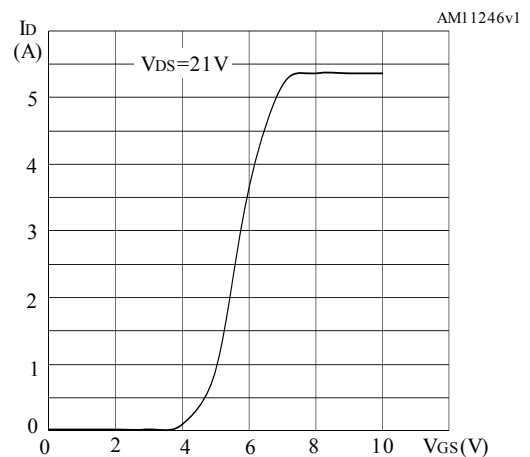


Figure 5. Typical gate charge characteristics

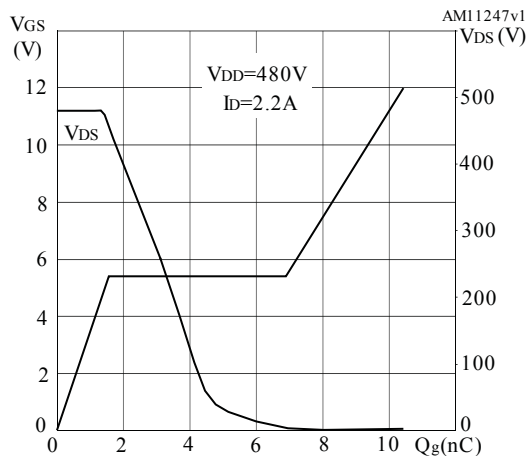


Figure 6. Typical drain-source on-resistance

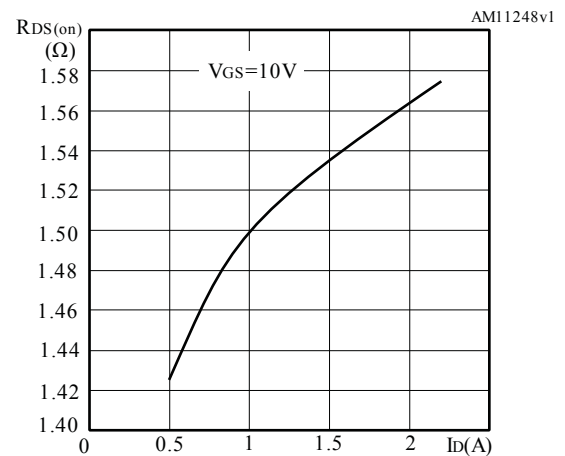


Figure 7. Typical capacitance characteristics

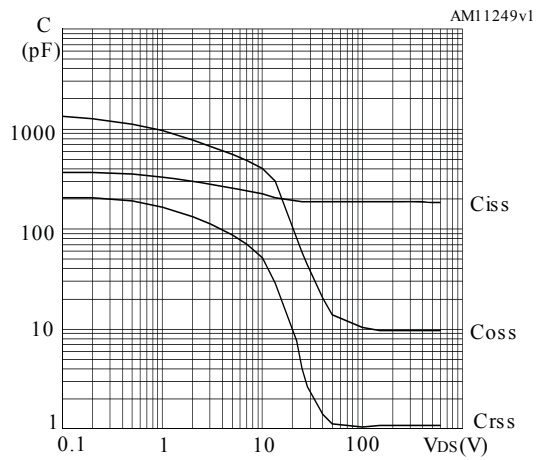


Figure 8. Typical output capacitance stored energy

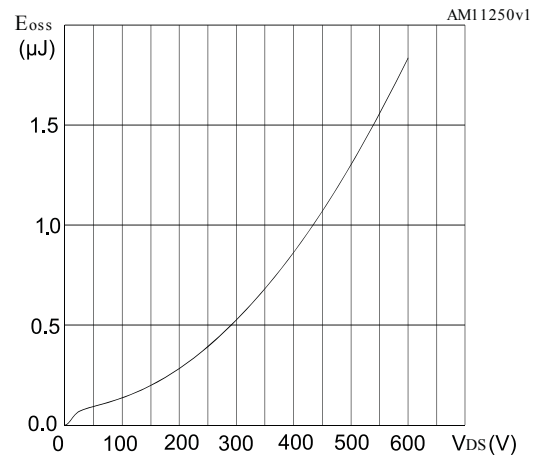


Figure 9. Normalized gate threshold vs temperature

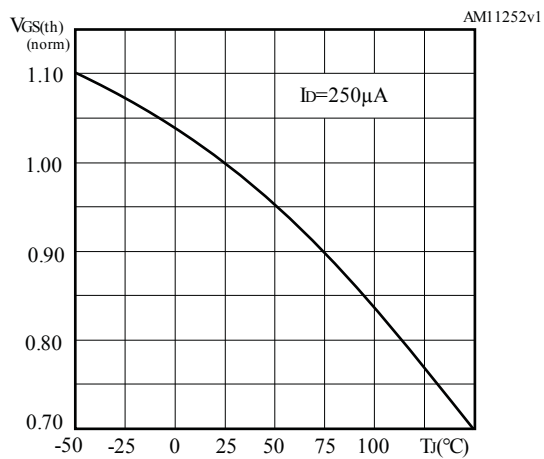


Figure 10. Normalized on-resistance vs temperature

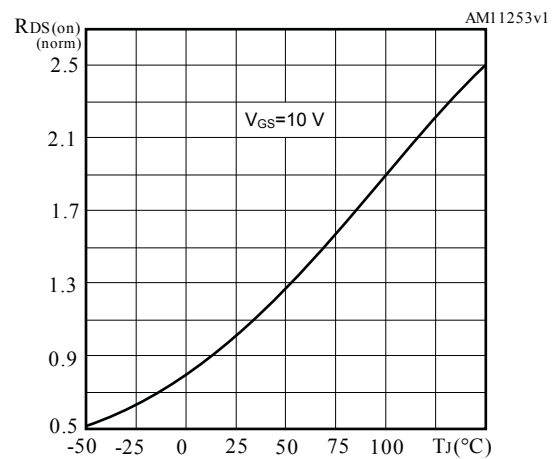


Figure 11. Normalized breakdown voltage vs temperature

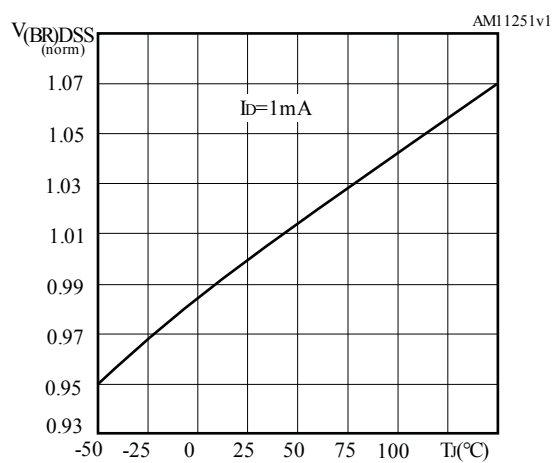
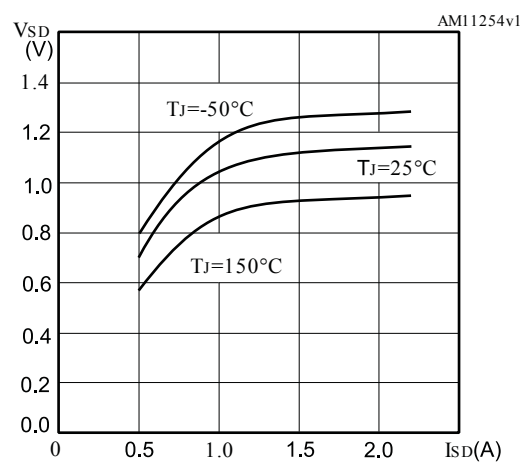
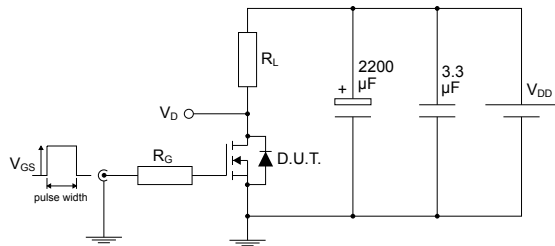


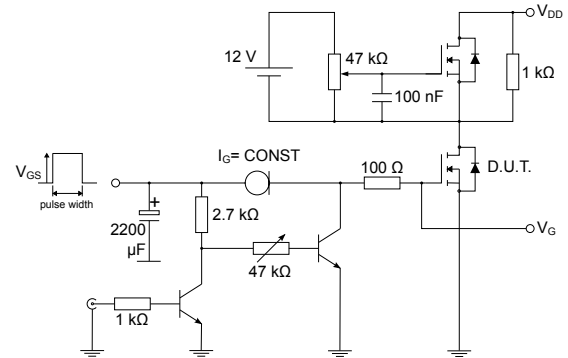
Figure 12. Typical reverse diode forward characteristics



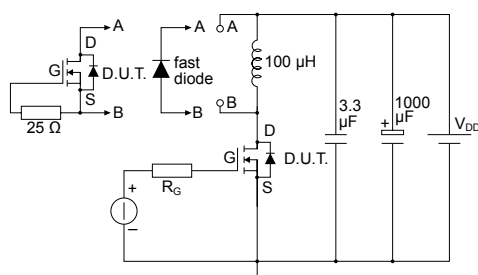
3 Test circuits

Figure 13. Test circuit for resistive load switching times


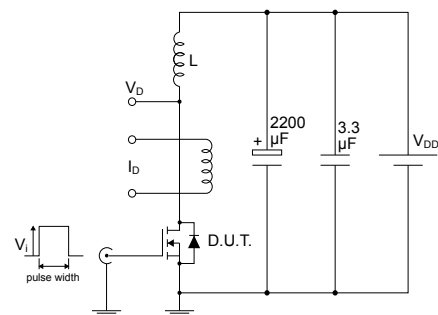
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Figure 14. Test circuit for gate charge behavior


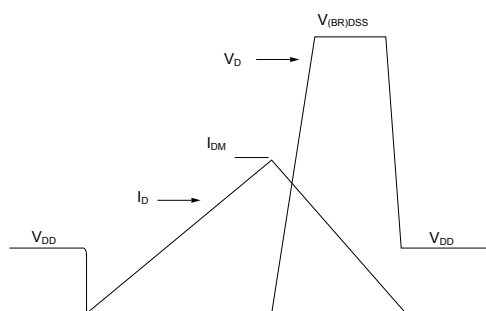
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Figure 15. Test circuit for inductive load switching and diode recovery times


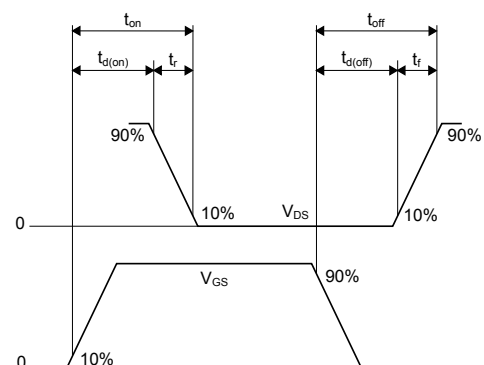
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Figure 16. Unclamped inductive load test circuit


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Figure 17. Unclamped inductive waveform


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Figure 18. Switching time waveform


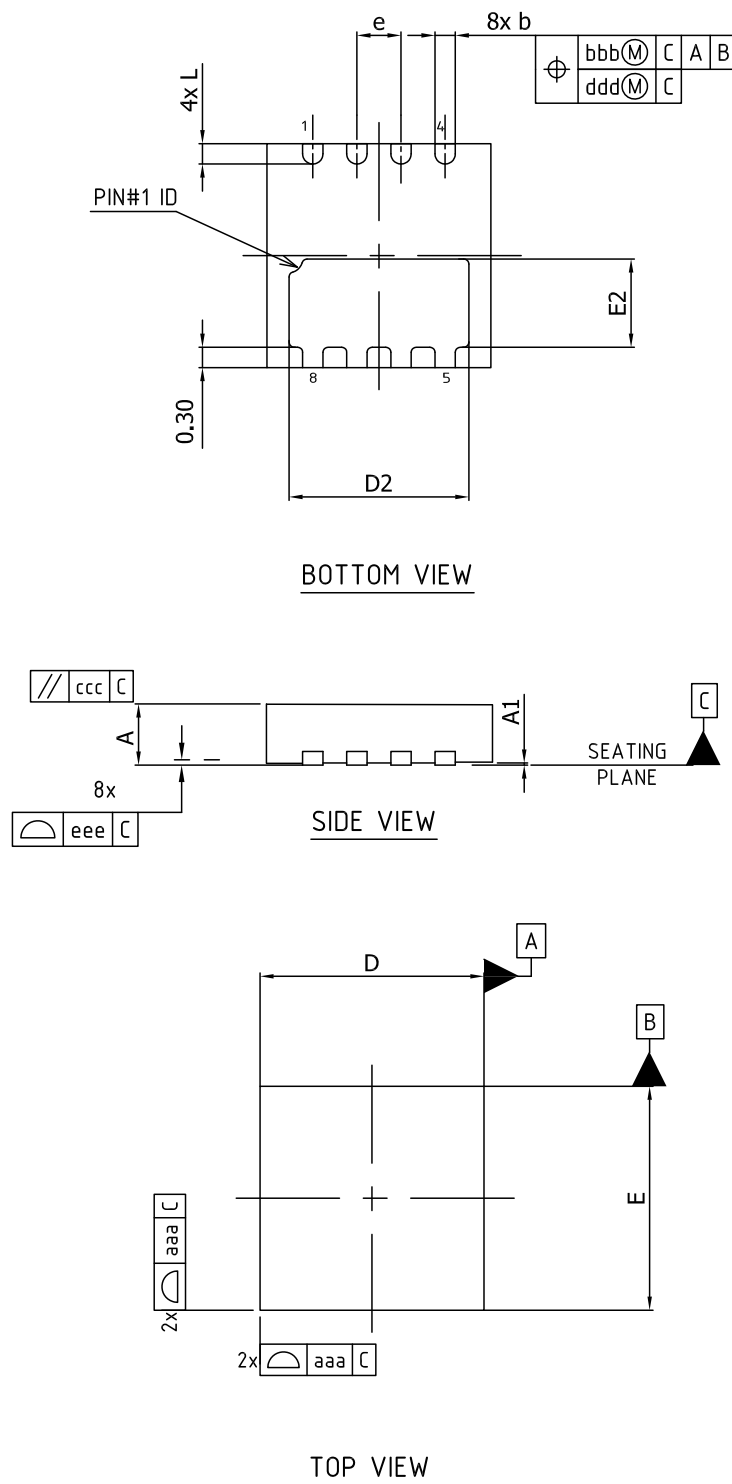
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 PowerFLAT 3.3x3.3 HV package information

Figure 19. PowerFLAT 3.3x3.3 HV package outline

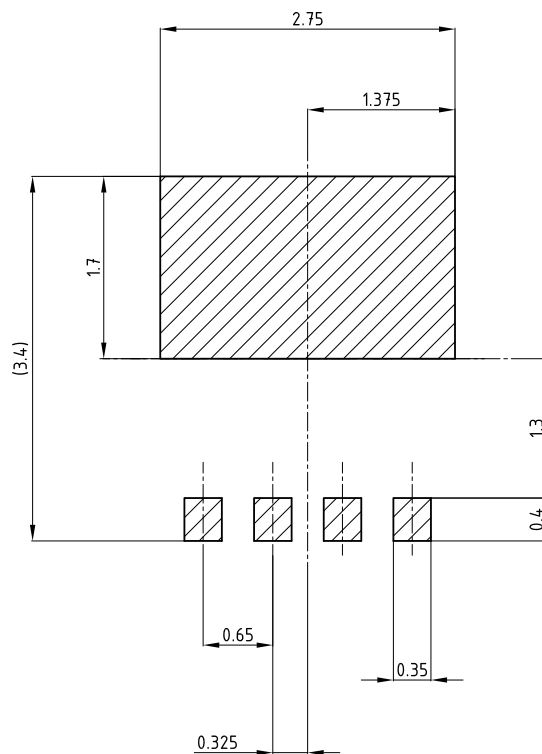


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Table 7. PowerFLAT 3.3x3.3 HV package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.90	1.00
A1	0	0.02	0.05
b	0.25	0.30	0.40
D		3.30	
D2	2.50	2.65	2.75
E		3.30	
E2	1.15	1.30	1.40
e		0.65	
L	0.20	0.30	0.40
aaa		0.10	
bbb		0.10	
ccc		0.10	
ddd		0.05	
eee		0.08	

Figure 20. PowerFLAT 3.3x3.3 HV recommended footprint (dimensions are in mm)



8374983_footprint

Revision history

Table 8. Document revision history

Date	Version	Changes
12-Mar-2012	1	First release.
19-Nov-2014	2	Document status changed from preliminary to production data. Updated <i>Figure 1.: Internal schematic diagram</i> , <i>Figure 2.: Safe operating area</i> , <i>Figure 3.: Thermal impedance</i> and <i>Figure 12.: Normalized $V_{(BR)DSS}$ vs temperature</i> . Updated <i>Table 5.: Dynamic</i> and <i>Table 7.: Source drain diode</i> . Minor text changes.
26-May-2022	3	Modified marking on cover page Updated <i>Figure 1. Safe operating area</i> Modified I_{SDM} value in <i>Table 6. Source-drain diode</i> Updated <i>Section 4.1 PowerFLAT 3.3x3.3 HV package information</i> Minor text changes.

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